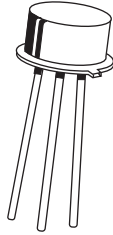


CM5160

**PNP HIGH FREQUENCY
SILICON TRANSISTOR**



JEDEC TO-39 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CM5160 is a silicon PNP RF transistor, mounted in a hermetically sealed package, designed for high frequency amplifier and non-saturated switching applications. This device is a replacement for the 2N5160.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

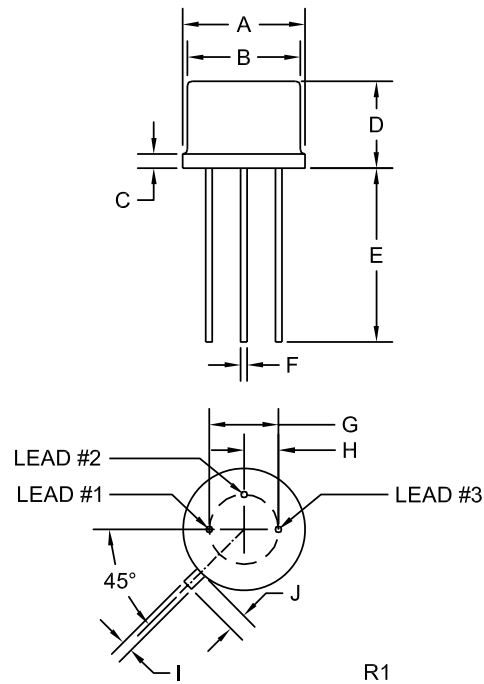
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C	400	mA
Power Dissipation	P_D	1.0	W
Power Dissipation ($T_C=25^{\circ}\text{C}$)	P_D	5.0	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +200	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=28\text{V}$			1.0	μA
I_{CES}	$V_{CE}=60\text{V}$			100	μA
I_{CEO}	$V_{CE}=28\text{V}$			20	μA
BV_{CEO}	$I_C=5.0\text{mA}$	40			V
BV_{EBO}	$I_E=100\mu\text{A}$	4.0			V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=50\text{mA}$	10			
f_T	$V_{CE}=15\text{V}, I_C=50\text{mA}, f=200\text{MHz}$	500			MHz
C_{cb}	$V_{CB}=28\text{V}, I_E=0, f=0.1 \text{ to } 1.0\text{MHz}$			4.0	pF

R1 (18-November 2005)

JEDEC TO-39 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) EMITTER
- 2) BASE
- 3) COLLECTOR

MARKING CODE:

FULL PART NUMBER

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

R1 (18-November 2005)